

ABSTRACT OF THE DISCLOSURE

Disclosed is an organic stripping composition and a method of etching a semiconductor device in which the generation of an Si pitting phenomenon can be prevented. The composition includes a compound including a hydroxyl ion (OH^-), a compound including a fluorine ion (F^-) and a sufficient amount of an oxidizing agent to control the pH of the composition within the range of from about 6.5 to about 8.0. The method includes dry etching an oxide by a dry etching using a plasma, and then ashing the etched oxide using an ashing process to remove an organic material. The method further includes supplying the organic stripping composition to remove residues including any residual organic material, a metal polymer, and an oxide type polymer. The stripping composition is stable onto various metals and does not induce the Si pitting phenomenon.